



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-323 Plastic-Encapsulate DIODE

BAW56W

SWITCHING DIODE

FEATURES

Power dissipation

P_D : 200 mW ($T_{amb}=25^{\circ}C$)

Collector current

I_O : 150 mA

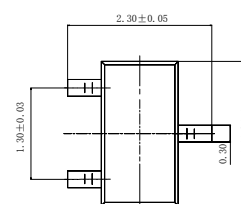
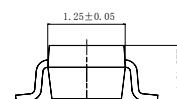
Collector-base voltage

V_R : 75 V

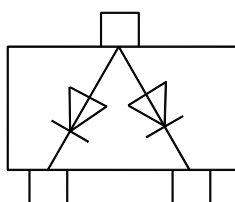
Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

SOT-323



Unit: mm



Marking: KJC

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)R}$	$I_R=100\mu A$	75		V
Reverse voltage leakage current	I_R	$V_R=75V$		2.5	μA
Forward voltage	V_F	$I_F=1mA$ $I_F=10mA$ $I_F=50mA$ $I_F=150mA$		715 855 1000 1250	mV
Diode capacitance	C_D	$V_R=0V, f=1MHz$		2	pF
Reveres recovery time	t_{rr}	$I_F=I_R=10mA$ $I_{rr}=0.1 \times I_R$		4	nS